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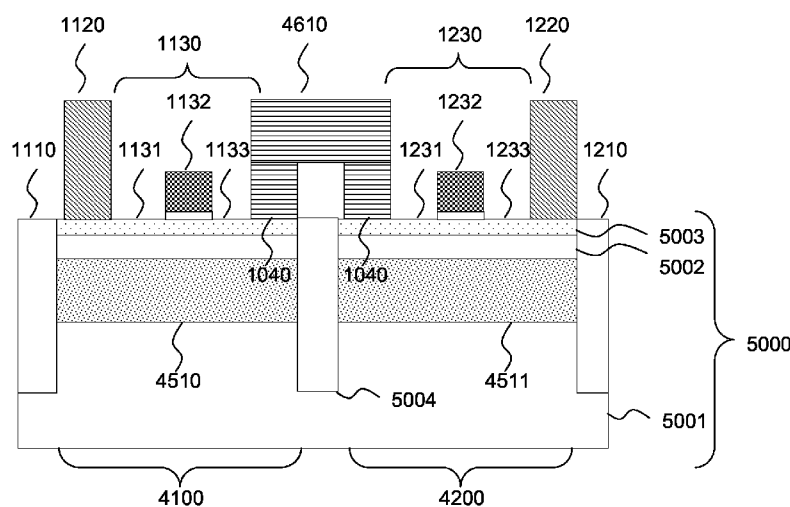
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(54) Title: BACK GATE IN SELECT TRANSISTOR FOR EDAM

Fig. 5



(57) Abstract: The present invention relates to an eDRAM memory element comprising a first storage node (1120, 1220), a bitline node (1040) for accessing the value stored in the storage node, and a select transistor (1130, 1230), controlling access from the bitline node to the storage node, wherein the select transistor has a front gate (1132, 1232) and a back gate (4510, 4511).